

L Number	Hits	Search Text	DB	Time stamp
-	42	"5302966"	USPAT	2004/08/09 07:44
-	12	"5587329"	USPAT	2004/08/09 08:57
-	34744	high\$1voltage low\$1voltage	USPAT; US-PGPUB	2004/08/09 10:07
-	535	(high\$1voltage low\$1voltage) and (silicon\$1on\$1insulat\$5)	USPAT; US-PGPUB	2004/08/09 08:58
-	958	(high\$1voltage low\$1voltage) and (soi silicon\$1on\$1insulat\$5)	USPAT; US-PGPUB	2004/08/09 08:59
-	305	((high\$1voltage low\$1voltage) and (soi silicon\$1on\$1insulat\$5)) and (thicker with (device near region) (semiconductor near layer) (low\$1voltage near region))	USPAT; US-PGPUB	2004/08/09 09:05
-	3	(high\$1voltage near region) and (low\$1voltage near region) and soi	USPAT; US-PGPUB	2004/08/09 10:11
-	2	(high\$1voltage near device) and (low\$1voltage near device) and soi	USPAT; US-PGPUB	2004/08/09 10:32
-	279	257/500.cccls.	USPAT; US-PGPUB	2004/08/09 11:37
-	559	438/479.cccls. not (257/500.cccls.)	USPAT; US-PGPUB	2004/08/09 12:47
-	80	438/295.cccls. not (438/479.cccls. 257/500.cccls.)	USPAT; US-PGPUB	2004/08/09 12:59
-	53	438/219.cccls. not (438/295.cccls. 438/479.cccls. 257/500.cccls.)	USPAT; US-PGPUB	2004/08/09 13:07
-	140	438/224.cccls. not (438/219.cccls. 438/295.cccls. 438/479.cccls. 257/500.cccls.)	USPAT; US-PGPUB	2004/08/09 13:22
-	291	438/404.cccls. not (438/224.cccls. 438/219.cccls. 438/295.cccls. 438/479.cccls. 257/500.cccls.)	USPAT; US-PGPUB	2004/08/09 14:03
-	123	438/412.cccls. not (438/404.cccls. 438/224.cccls. 438/219.cccls. 438/295.cccls. 438/479.cccls. 257/500.cccls.)	USPAT; US-PGPUB	2004/08/10 18:52
-	1560	(silicon\$1on\$1insulator soi) and (nitride with oxide with remov\$5)	USPAT; US-PGPUB	2004/08/10 13:06
-	216	((silicon\$1on\$1insulator soi) and (nitride with oxide with remov\$5)) and (high adj voltage\$1)	USPAT; US-PGPUB	2004/08/10 15:26
-	1	"10367265"	JPO; DERWENT	2004/08/10 15:12
-	1791	(silicon\$1on\$1insulator soi) and ((nitride with oxide) same thin\$5)	USPAT;	2004/08/10 15:37
-	992	((silicon\$1on\$1insulator soi) and ((nitride with oxide) same thin\$5)) and ((nitride with oxide) with thin\$5)	USPAT; US-PGPUB	2004/08/10 15:34
-	3022	(silicon\$1on\$1insulator soi) and (thin\$5 with ((semiconductor near layer) (silicon near layer) (high\$1voltage near (region area)) (low\$1voltage near (region area))))	USPAT; US-PGPUB	2004/08/10 15:42
-	1486	((silicon\$1on\$1insulator soi) and (thin\$5 with ((semiconductor near layer) (silicon near layer) (high\$1voltage near (region area)) (low\$1voltage near (region area)))) and (((remov\$5 etch\$5) oxide) with thin\$5 with ((semiconductor near layer) (silicon near layer) (high\$1voltage near (region area)) (low\$1voltage near (region area))))	USPAT; US-PGPUB	2004/08/10 15:45
-	2498	(438/275.cccls. 257/347.cccls.) not (438/412.cccls. 438/404.cccls. 438/224.cccls. 438/219.cccls. 438/295.cccls. 438/479.cccls. 257/500.cccls.)	USPAT; US-PGPUB	2004/08/10 19:00
-	253	((438/275.cccls. 257/347.cccls.) not (438/412.cccls. 438/404.cccls. 438/224.cccls. 438/219.cccls. 438/295.cccls. 438/479.cccls. 257/500.cccls.)) and (high adj voltage) and (low adj voltage)	USPAT; US-PGPUB	2004/08/10 19:01
-	47	((438/275.cccls. 257/347.cccls.) not (438/412.cccls. 438/404.cccls. 438/224.cccls. 438/219.cccls. 438/295.cccls. 438/479.cccls. 257/500.cccls.)) and (high adj voltage) and (low adj voltage)) and (region near (thick\$5 thin\$7))	USPAT; US-PGPUB	2004/08/10 19:01

-		1	"20040121547"	DERWENT	2004/08/10 19:11
-		4	(U11-C18A3 and U12-D02A3 and U12-D02A4 and U12-Q).epi.	DERWENT	2004/08/10 19:11
-		1926	(L04-C07 and L04-C12).cpi.	DERWENT	2004/08/10 19:12
-		37	((L04-C07 and L04-C12).cpi.) and soi	DERWENT	2004/08/10 19:12
-		17	"5780900"	USPAT	2004/08/11 12:30
-		14	"5097314"	USPAT	2004/08/11 13:54
-		22	(silicon\$ion\$1insulator soi) and ((high adj voltage) near (area region section portion)) and ((low adj voltage) near (area region section portion))	USPAT	2004/08/11 14:07